

Description

The VST15N560 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

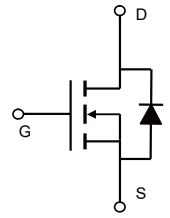
- $V_{DS} = 150V, I_D = 20A$
 $R_{DS(ON)} = 56m\Omega$ (typical) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 68m\Omega$ (typical) @ $V_{GS} = 4.5V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification



TO-252



Schematic

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST15N560	VST15N560-T2	TO-252	Ø330mm	16mm	2500 units

Absolute Maximum Ratings ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	20	A
Drain Current-Continuous($T_C = 100^\circ C$)	$I_D(100^\circ C)$	14	A
Pulsed Drain Current	I_{DM}	80	A
Maximum Power Dissipation	P_D	68	W
Derating factor		0.45	W/°C
Drain Source voltage slope, $V_{DS} \leq 150 V$	dv/dt	50	V/ns
Reverse diode dv/dt , $V_{DS} \leq 150 V$, $I_{SD} < I_D$	dv/dt	10	V/ns
Single pulse avalanche energy (Note 5)	E_{AS}	30	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	°C

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	2.2	$^{\circ}\text{C/W}$
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Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

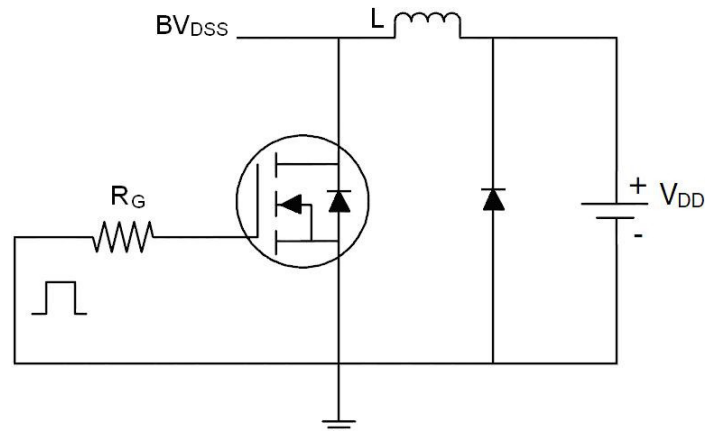
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	150	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.3	1.9	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	56	62	mΩ
		V _{GS} =4.5V, I _D =10A		68	82	
Gate resistance	R _G		-	10	-	Ω
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =10A	-	15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =75V, V _{GS} =0V, F=1.0MHz	-	799		PF
Output Capacitance	C _{oss}		-	74.4		PF
Reverse Transfer Capacitance	C _{rss}		-	11.1		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =75V, R _L =7.5Ω V _{GS} =10V, R _G =3Ω	-	10.5	-	nS
Turn-on Rise Time	t _r		-	6	-	nS
Turn-Off Delay Time	t _{d(off)}		-	14.5	-	nS
Turn-Off Fall Time	t _f		-	3.5	-	nS
Total Gate Charge	Q _g	V _{DS} =75V, I _D =10A, V _{GS} =10V	-	15	-	nC
Gate-Source Charge	Q _{gs}		-	4.5	-	nC
Gate-Drain Charge	Q _{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =10A	-	-	1.2	V
Diode Forward Current (Note 2)	I _S		-	-	20	A
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S	-	29.5	-	nS
Reverse Recovery Charge	Q _{rr}	di/dt = 100A/μs(Note3)	-	132	-	nC

Notes:

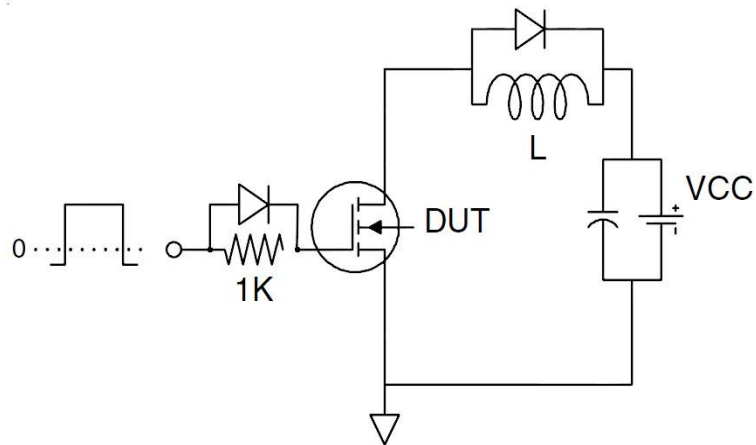
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_G=25\Omega$

Test Circuit

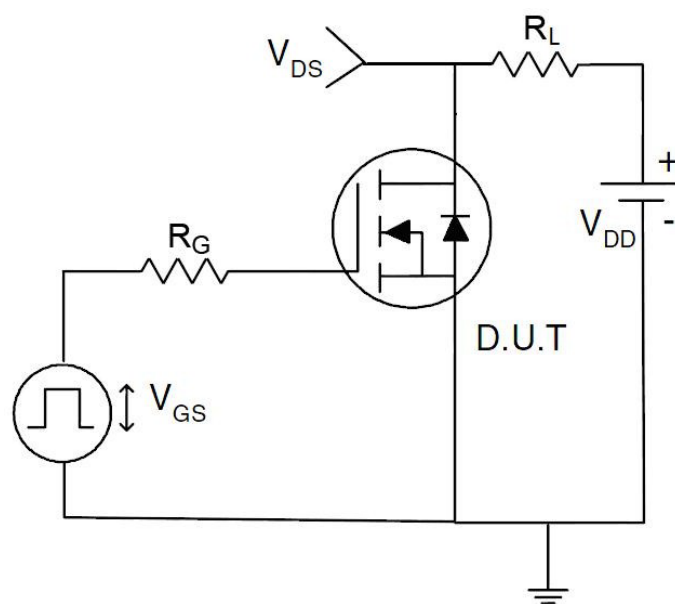
1) E_{AS} test Circuit



2) Gate charge test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics

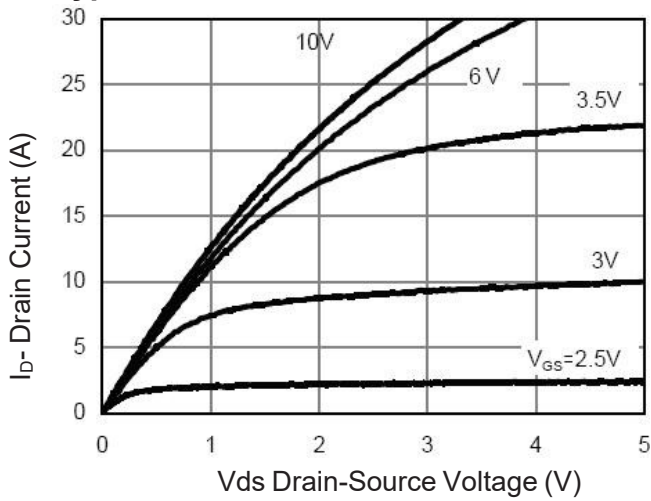


Figure 1 Output Characteristics

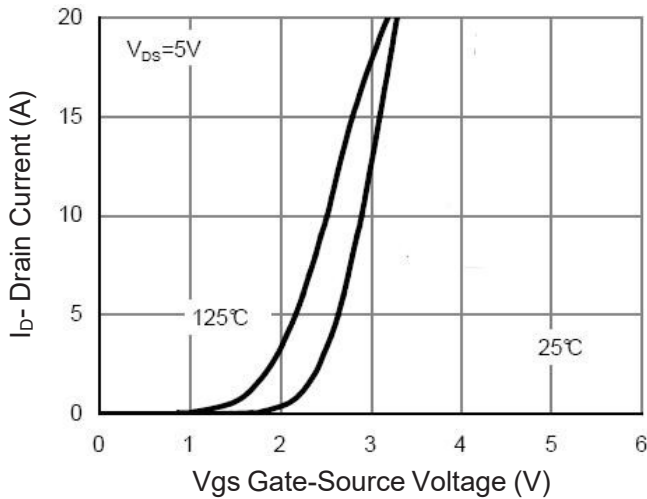


Figure 2 Transfer Characteristics

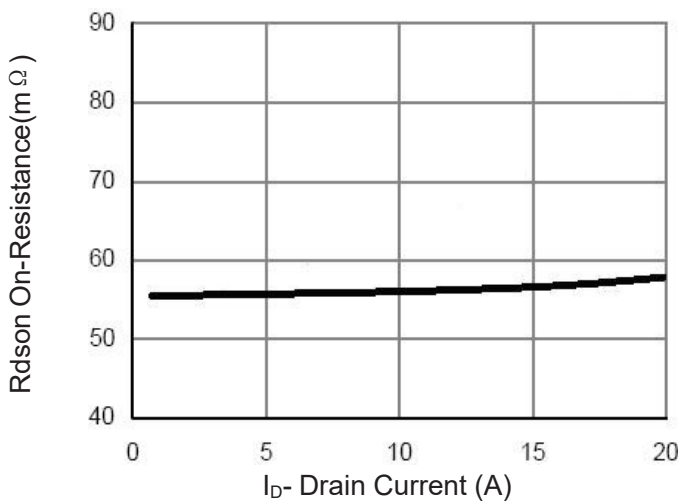


Figure 3 Rdson- Drain Current

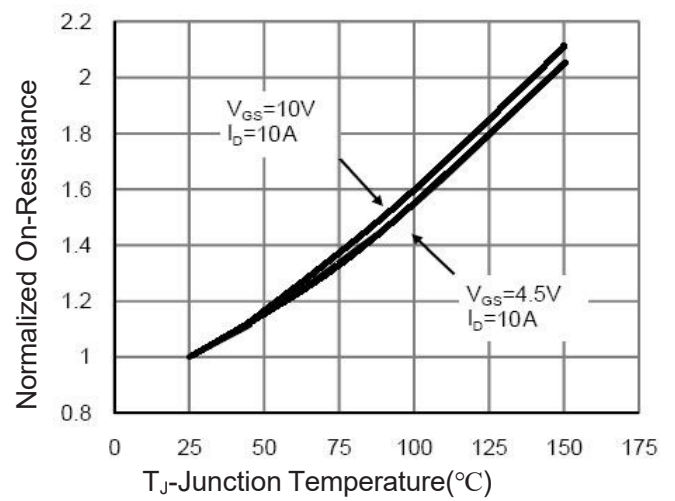


Figure 4 Rdson-Junction Temperature

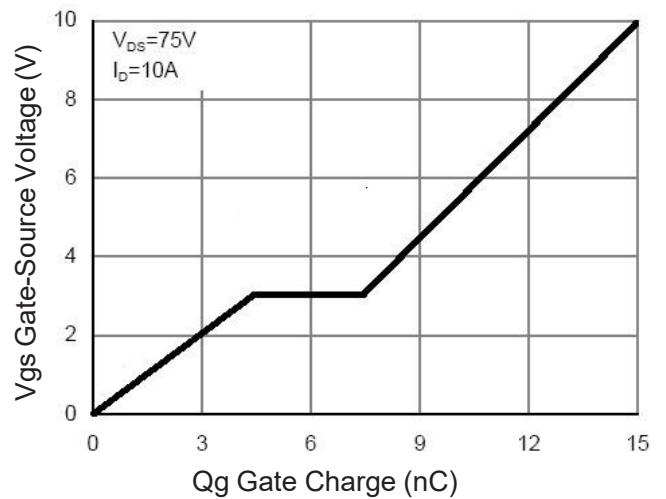


Figure 5 Gate Charge

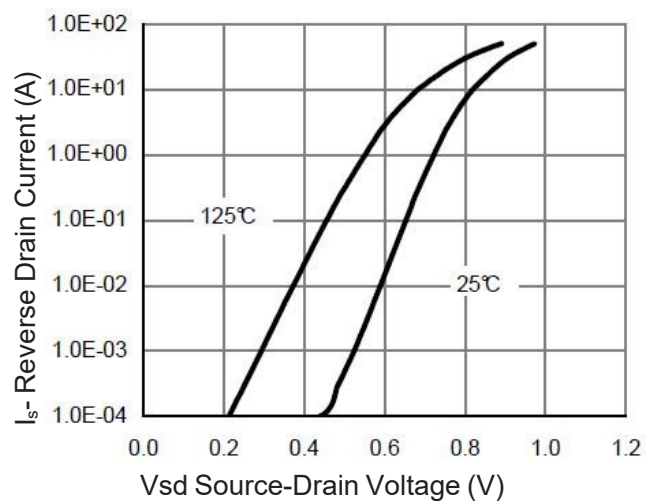
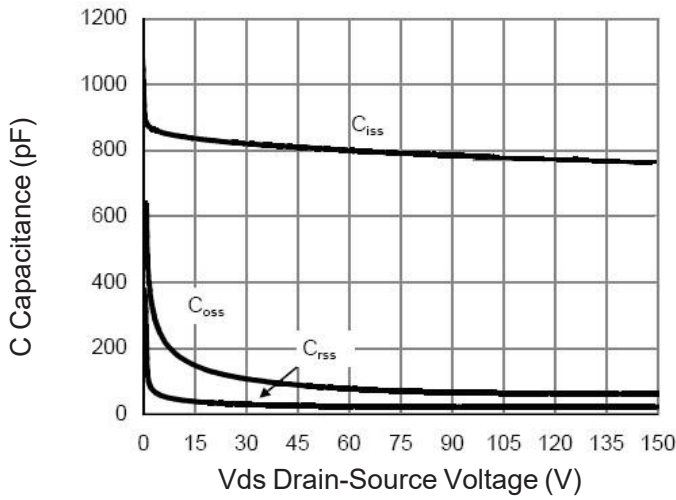
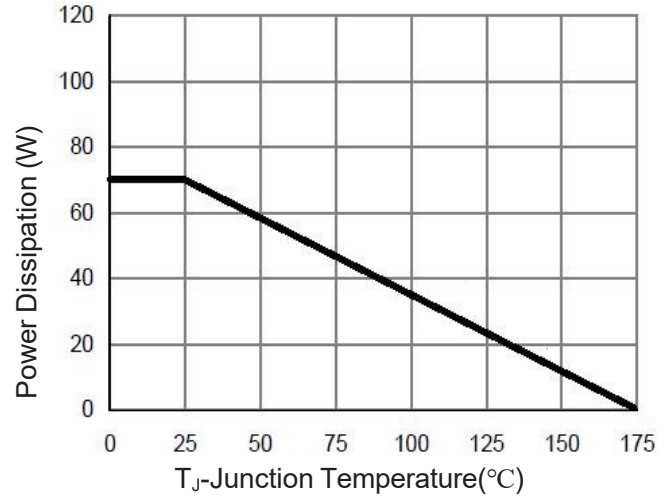
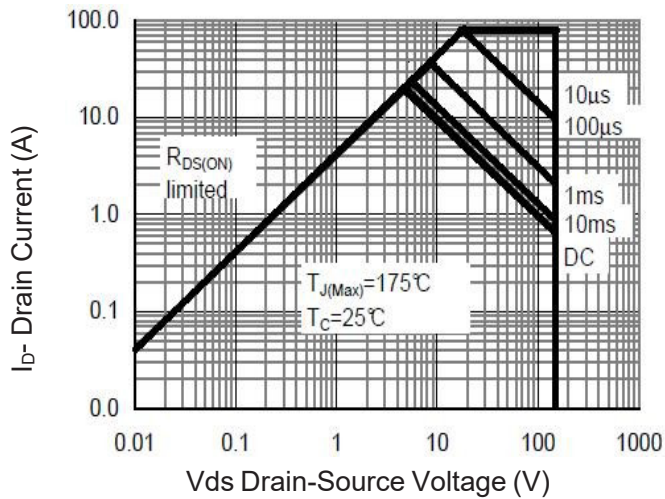
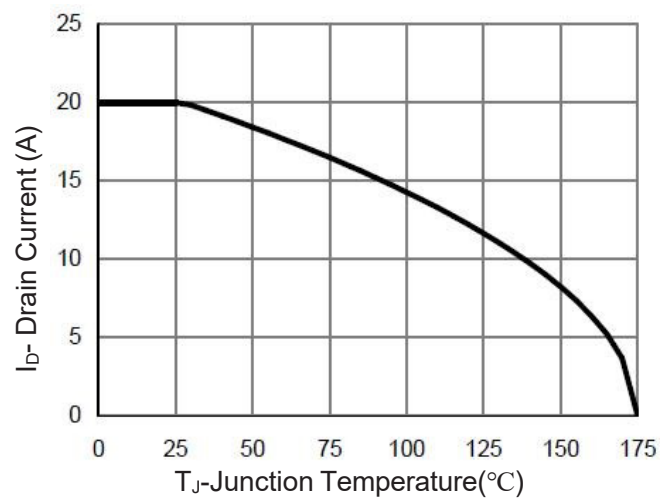
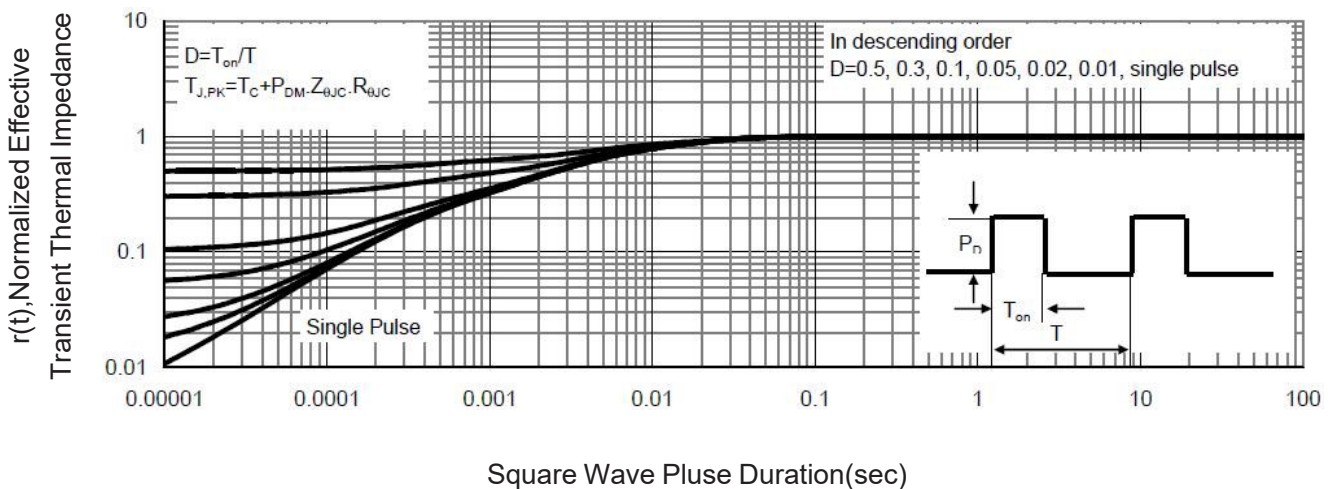


Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area

Figure 10 Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance